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Rec'd PCT/PTO 26 MAR 2002

ATTORNEY'S DOCKET NO: 020264

U.S. DEPARTMENT OF COMMERCE, PATENT AND TRADEMARK OFFICE		DATE: March 26, 2002
TRANSMITTAL LETTER TO THE UNITED STATES DESIGNATED/ELECTED OFFICE (DO/EO/US) CONCERNING A FILING UNDER 35 U.S.C. 371		U.S. APPL. NO. (if known): 10/088489
INTERNATIONAL APPLICATION NO.: PCT/JP00/06504	INTERNATIONAL FILING DATE: SEPTEMBER 22, 2000	PRIORITY DATE CLAIMED: SEPTEMBER 27, 1999
TITLE OF INVENTION: ELECTROLESS PLATING METHOD		
APPLICANT(S) FOR DO/EO/US: Tetsuhiro NAKAMURA		
Applicant hereby submits to the United States Designated/Elected Office (DO/EO/US) the following items and other information:		
<p>1. <input checked="" type="checkbox"/> This is a FIRST submission of items concerning a filing under 35 U.S.C. 371.</p> <p>2. <input type="checkbox"/> This is a SECOND or SUBSEQUENT submission of items concerning a filing under 35 U.S.C. 371.</p> <p>3. <input checked="" type="checkbox"/> This express request to begin national examination procedures (35 USC 371(f)) at any time rather than delay examination until the expiration of the time limit set in 35 USC 371(b) and PCT Articles 22 and 39(1).</p> <p>4. <input checked="" type="checkbox"/> A proper Demand for International Preliminary Examination was made by the 19th month from the earliest claimed priority date.</p> <p>5. <input checked="" type="checkbox"/> A copy of the International Application as filed (35 U.S.C. 371(c)(2)):</p> <p style="margin-left: 20px;">a. <input type="checkbox"/> is transmitted herewith (required only if not transmitted by the International Bureau).</p> <p style="margin-left: 20px;">b. <input checked="" type="checkbox"/> has been transmitted by the International Bureau.</p> <p style="margin-left: 20px;">c. <input type="checkbox"/> is not required, as the application was filed in the United States Receiving Office (RO/US).</p> <p>6. <input checked="" type="checkbox"/> A translation of the International Application into English (35 U.S.C. 371(c)(2)).</p> <p>7. <input checked="" type="checkbox"/> Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. 371(c)(3))</p> <p style="margin-left: 20px;">a. <input type="checkbox"/> are transmitted herewith (required only if not transmitted by the International Bureau).</p> <p style="margin-left: 20px;">b. <input type="checkbox"/> have been transmitted by the International Bureau.</p> <p style="margin-left: 20px;">c. <input type="checkbox"/> have not been made; however, the time limit for making such amendments has NOT expired.</p> <p style="margin-left: 20px;">d. <input checked="" type="checkbox"/> have not been made and will not be made.</p> <p>8. <input type="checkbox"/> A translation of the amendments to the claims under PCT Article 19 (35 U.S.C. 371(c)(3)).</p> <p>9. <input checked="" type="checkbox"/> An oath or declaration of the inventor(s) (35 U.S.C. 371(c)(4)).</p> <p>10. <input checked="" type="checkbox"/> A translation of the annexes to the International Preliminary Examination Report under PCT Article 36 (35 U.S.C. 371(c)(5)).</p> <p>ITEMS 11. TO 16. BELOW CONCERN OTHER DOCUMENT(S) OR INFORMATION INCLUDED:</p> <p>11. <input checked="" type="checkbox"/> An Information Disclosure Statement under 37 CFR 1.97 and 1.98 together with the international search report and 3 Refs..</p> <p>12. <input checked="" type="checkbox"/> An assignment document for recording. A separate cover sheet in compliance with 37 CFR 3.28 and 3.31 is included. ASSIGNEE NAME AND ADDRESS: CITIZEN WATCH CO., LTD., Tokyo, Japan Please publish the assignee data with the application.</p> <p>13. <input checked="" type="checkbox"/> A FIRST preliminary amendment.</p> <p>14. <input type="checkbox"/> A substitute specification.</p> <p>15. <input type="checkbox"/> A change of power of attorney and/or address letter.</p> <p>16. <input checked="" type="checkbox"/> Other items or information: 10 sheets of drawings.</p>		

U.S. APPLICATION NO. (if known) 10/088489	INTERNATIONAL APPLICATION NO. PCT/JP00/06504	DATE: March 26, 2002			
17. <input checked="" type="checkbox"/> The following fees are submitted:					
Basic National Fee (37 CFR 1.492(a)(1)-(5): Search Report has been prepared by the EPO or JPO: \$890.00 International preliminary examination fee paid to USPTO (37 CFR 1.482) \$710.00 No international preliminary examination fee paid to USPTO (37 CFR 1.482) but international search fee paid to USPTO (37 CFR 1.445(a)(2)) \$740.00 Neither international preliminary examination fee (37 CFR 1.482) nor international search fee (37 CFR 1.445(a)(2)) paid to USPTO \$1040.00 International preliminary examination fee (37 CFR 1.482) and all claims satisfied provisions of PCT Article 33(2)-(4) \$100.00	CALCULATIONS	PTO USE ONLY			
ENTER APPROPRIATE BASIC FEE AMOUNT =		\$ 890.00			
Surcharge of \$130.00 for furnishing the oath or declaration later than __ 20 30 months from the earliest claimed priority date (37 CFR 1.492(e)).					
CLAIMS	NUMBER FILED	NUMBER EXTRA	RATE		
TOTAL	22-20 =	2	X \$ 18.00	\$ 36.00	
INDEPENDENT	11 - 3 =	8	X \$ 84.00	\$ 672.00	
Multiple dependent claims(s) (if applicable)			+ \$280.00		
TOTAL OF ABOVE CALCULATIONS =				\$1,598.00	
Reduction by 1/2 for filing by small entity, if applicable. (Note 37 CFR 1.9, 1.27, 1.28).					
SUBTOTAL =				\$1,598.00	
Processing fee of \$130.00 for furnishing the English translation later than __ 20 30 months from the earliest claimed priority date (37 CFR 1.492(f)). +					
TOTAL NATIONAL FEE =				\$1,598.00	
Fee for recording the enclosed assignment (37 CFR 1.21(h)). The assignment must be accompanied by an appropriate cover sheet (37 CFR 3.28, 3.31).				\$ 40.00	
\$40.00 per property +					
TOTAL FEES ENCLOSED =				\$1,638.00	
Amount to be:				refunded \$ _____	charged \$ _____

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JC13 Rec'd PCT/PTO 26 MAR 2002

ATTORNEY'S DOCKET NO: 020264

U.S. APPLICATION NO. (if known) 10/088489	INTERNATIONAL APPLICATION NO. PCT/JP00/06504	DATE: March 26, 2002
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a. ☒ A check in the amount of \$1,638.00 to cover the above fees is enclosed. (\$890.00 for basic filing fee; \$36.00 for 2 additional claims; \$672.00 for 8 additional independent claims and \$40.00 for assignment recordation fee). (This paper is filed in triplicate)

b. ☐ Please charge my Deposit Account No. 01-2340 in the amount of \$ to cover the above fees. (A duplicate copy of this sheet is enclosed.)

c. ☒ The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Deposit Account No. 01-2340.

NOTE: Where an appropriate time limit under 37 CFR 1.494 or 1.495 has not been met, a petition to revive (37 CFR 1.137(a) or (b)) must be filed to request that the application be restored to pending status.

Send All Correspondence To:


23850
 PATENT TRADEMARK OFFICE

William L. Brooks
SIGNATURE

William L. Brooks
NAME

34,129
REGISTRATION NUMBER

WLB/yap

ARMSTRONG, WESTERMAN & HATTORI, LLP
 Suite 1000, 1725 K Street, N W
 Washington, D C 20006
 Tel: (202) 659-2930
 Fax: (202) 887-0357

JC13 Rec'd PCT/PTO 26 MAR 2002

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **Tetsuhiro NAKAMURA**

Serial Number: **Not Yet Assigned**

(§ 371 of international application No. PCT/JP00/06504)

Filed: **March 26, 2002**

For: **ELECTROLESS PLATING METHOD**

SUBMISSION OF SUBSTITUTE PAGES FOR PCT 34 AMENDMENT
AND PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

March 26, 2002

Sir:

This application is the U.S. national stage under 35 USC § 371 of the above-identified international patent application.

IN THE SPECIFICATION:

Please enter the attached substitute sheets for pages 1, 5, 5/1, 6-10 and 10/1. The substitute sheets incorporate into the English language translation of the international application amendments presented in the international stage under PCT Article 34.

IN THE CLAIMS:

Please amend the following claims as follows:

1. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the surface of the object to be plated, without the metallic film formed thereon and the metal in contact therewith.

3. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath,

wherein said object to be plated is made of plural kinds of constituent materials.

4. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, wherein said object to be plated is a thermoelectric semiconductor.

6. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on one of end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

dipping said thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and the other end face of the respective thermoelectric semiconductors, on the side thereof, opposite from the end face on which the metallic film is formed;

removing said metallic film and a portion of the electroless plating film covering up the metallic film; and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the end face of the respective thermoelectric semiconductors from which the metallic film is removed.

7. (Amended) An electroless plating method comprising the steps of:

causing a metal on which an electroless plating film can be deposited to be in contact with a part of at least one of end faces of respective thermoelectric semiconductors of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

dipping the thermoelectric device block having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the respective thermoelectric semiconductors, except the part thereof, in contact with said metal,

separating the metal in contact with the respective thermoelectric semiconductors therefrom;
and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with said metal.

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8. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans said respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face thereof.

9. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on either an end face or the other end face of respective insulation layers, alternately, on the sides of both end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans the respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers; and

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dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face and the other end face thereof.

10. (Amended) An electroless plating method according to claim 6, wherein use is made of said thermoelectric device block provided with an exposed outer sidewall face of respective thermoelectric semiconductors positioned at opposite ends in the direction along which the respective thermoelectric semiconductors are arranged, and an electroless plating film is also formed on the exposed outer sidewall faces of respective thermoelectric semiconductors positioned at opposite ends as well in said step of forming the electroless plating film.

11. (Amended) An electroless plating method according to claim 6, further comprising the step of rendering the end face of the thermoelectric device block into a rough surface prior to the step of forming the electroless plating film on said thermoelectric device block.

12. (Amended) An electroless plating method according to claim 6, further comprising the step of cleaning said thermoelectric device block before or after the step of forming the electroless plating film on said thermoelectric device block.

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Please add the following new claims:

13. An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied;

dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the object to be plated, containing the metallic film or the metal;

removing the metallic film or the metal, and portions of the electroless plating film, covering up the metallic film or the metal, from the object to be plated; and

dipping again the object to be plated subjected to the steps described above in the electroless plating bath, wherein the object to be plated is made of plural kinds of constituent materials.

14. An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied;

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16. An electroless plating method according to claim 1, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

17. An electroless plating method according to claim 2, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

18. An electroless plating method according to claim 3, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

19. An electroless plating method according to claim 13, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

20. An electroless plating method according to claim 1, wherein use is made of palladium, platinum or nickel as the metal on which the electroless plating film can be deposited.

21. An electroless plating method according to claim 15, wherein use is made of an insulating resin for the insulators.

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22. An electroless plating method according to claim 6, wherein use is made of an insulating resin for the insulation layers.

$\frac{1}{\sqrt{2}} \begin{pmatrix} 1 & i \\ 1 & -i \end{pmatrix}$

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REMARKS

The above amendment is submitted to place the claims in substantially the same conditions as to the claims which have been amended under Article 34 in the international application and to remove improper multiple dependency of the claims. An English translation of the annexes of the PCT international preliminary examination report is enclosed. Early and favorable action is awaited.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned “Version with marking to show changes made.”

In the event there are any additional fees required, please charge our Deposit Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP

Atty. Docket No. 020264
Suite 1000
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WLB/yap
Enclosures: Substitute sheets

William L. Brooks
Reg. No. 34,129

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The following claims have been amended as follows:

The following claims have been amended as follows:

1.(Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the surface of the object to be plated, without the metallic film formed thereon and the metal in contact therewith.

3. (Amended) An electroless plating method [according to claims 1 or 2,] comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the

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dipping said thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and the other end face of the respective thermoelectric semiconductors, on the side thereof, opposite from the end face on which the metallic film is formed;

removing said metallic film and a portion of the electroless plating film covering up the metallic film; and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the end face of the respective thermoelectric semiconductors from which the metallic film is removed.

7. (Amended) An electroless plating method comprising the steps of:

causing a metal on which an electroless plating film can be deposited to be in contact with a part of at least one of end faces of respective thermoelectric semiconductors of a thermoelectric device block formed integrally with a plurality of [bar-shaped] thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

dipping the thermoelectric device block having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the respective thermoelectric semiconductors, except the part thereof, in contact with said metal,

separating the metal in contact with the respective thermoelectric semiconductors therefrom;

and

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dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with said metal.

8. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of [bar-shaped] thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans said respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face thereof.

9. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on either an end face or the other end face of respective insulation layers, alternately, on the sides of both end faces of a thermoelectric device block formed integrally with a plurality of [bar-shaped]

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12. (Amended) An electroless plating method according to [any one of claims 6 to 9] claim 6, further comprising the step of cleaning said thermoelectric device block before or after the step of forming the electroless plating film on said thermoelectric device block.

(11.07.01)

AMENDMENT OF PROCEDURE
(Amendment under the provision of Article 11)

Commissioner of Patent Office

1. Indication of International Application

PCT/JP00/06504

2. Applicant

Name	CITIZEN WATCH Co., Ltd.
Address	1-12, Tanashicho 6-chome, Nishitokyo-shi, Tokyo 188-8511 Japan
Nationality	Japan
Residence	Japan

3. Agent

Name	(8093) OSAWA Takashi
Address	Room 818, Ikebukuro White House Bldg., 20-2, Higashi Ikebukuro 1-chome, Toshima-ku, Tokyo 170-0013 Japan

4. Object of Amendment	DESCRIPTION
	CLAIMS

5. Content of Amendment As per attached paper

(1) In the 11th line of page 1 of DESCRIPTION,
“respective thermoelectric semiconductors of a thermoelectric device block.” is amended to “metal or semiconductors, to which an electroless plating can not be directly applied. ”

(2) After “plating bath.” in the 24th line of page 5 of DESCRIPTION,
“, and forming an electroless plating film on the surface of the object to be plated, without the metallic film formed thereon and the metal in contact therewith. ” is added.

(3) In the 24th-25th line of page 6, in the 17th-18th line of page 7 , in the 10th-11th line of page 8 and 27th line of page 8-1st line of page 9 of DESCRIPTION,
“a plurality of bar-shaped thermoelectric semiconductors” is amended to “a plurality of thermoelectric semiconductors”

(4) Between the 1st line and the 2nd line of page 10 of DESCRIPTION, is amended to add as follows.

“And further, the present invention provides an electroless plating method comprising the steps of preparing an object to be plated, comprised of metal or semiconductors, to which an electroless plating can not be applied, and insulators, and forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of the object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, and dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the object to be plated, except for the insulators.

As the constituent material to which an electroless plating can not be applied,

use can be made of a metal or a semiconductor, to which an electroless plating can not be applied.

As the metal on which the electroless plating film can be deposited, use can be made of palladium, platinum or nickel.

An insulating resin is preferably used for the insulators or the insulation layers. ”

(5) Claims 1, 3, 4, 6, 7, 8 and 9 are amended as per attached papers and Claims 13, 14, 15, 16, 17, 18, 19, 20, 21 and 22 are added.

6. List of Attached Documents

(1) DESCRIPTION:	new pages 1, 5, 5/1, 6, 7, 8, 9, 10, and 10/1	1
(2) CLAIMS:	new pages 29, 29/1, 30, 30/1, 31, 32, 32/1, 33, 33/1, and 33/2	1

(Above-indicated pages and lines are based on the English translation of the original Japanese DESCRIPTION and CLAIMS.)

DESCRIPTION

ELECTROLESS PLATING METHOD

TECHNICAL FIELD

The invention relates to an electroless plating method for applying electroless plating to an object to be plated, made of a constituent material to which an electroless plating can not be directly applied, and in particular, to an electroless plating method suited for forming a conductive film on end faces of metal or semiconductors, to which an electroless plating can not be directly applied.

BACKGROUND TECHNOLOGY

As a thermoelectric device generates a voltage if the opposite ends thereof are maintained at different temperatures, the same is utilized for thermoelectric power generation, and conversely, if electric current is caused to flow therethrough, an exothermic reaction occurs at one end thereof while an endothermic reaction occurs at the other end thereof. Accordingly, the same is also utilized in a cooling apparatus, and so forth, making use of an endothermic phenomenon. Because such a thermoelectric device as described above is simple in construction, and has an advantage over other electric power generators in implementation of miniaturization, and so forth, hopes run high that the same will be applied to portable electronic equipment such as an electronic wrist watch.

The thermoelectric device is made up of a plurality of thermocouples arranged in series, each composed of a p-type

semiconductors, in a range of several to several tens of μm . The more minuscule the structure of the thermoelectric device, the more difficult it becomes to form the conductive films selectively only on the thermoelectric semiconductors. It is therefore a major problem in the fabrication of the thermoelectric device to selectively form the conductive films by electroless plating.

The invention has been developed to solve those problems, and an object of the invention is to provide an electroless plating method whereby conductive films can be formed even on the surface of a constituent material to which it is not possible to apply electroless plating, and further, to selectively form the conductive films uniform in thickness on end faces of respective thermoelectric semiconductors formed of a constituent material to the surface of which it is not possible to apply electroless plating, thereby enhancing productivity and reliability of a thermoelectric device as fabricated.

DISCLOSURE OF THE INVENTION

An electroless plating method according to the invention comprises the steps of forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied, and dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the surface of the object to be plated, without

the metallic film formed thereon and the metal in contact therewith.

Further, the electroless plating method according to the invention may comprise the steps of forming a metallic film made of a metal on

which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied, dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the object to be plated, containing the metallic film or the metal, removing the metallic film or the metal, and portions of the electroless plating film, covering up the metallic film or the metal, from the object to be plated, and dipping again the object to be plated subjected to the steps described above in the electroless plating bath.

With any of the electroless plating methods described above, the object to be plated may be made of plural kinds of constituent materials or may be a thermoelectric semiconductor.

Further, with any of the electroless plating methods described above, the electroless plating film may be formed so as to have a dual-layer structure comprised of not less than two metallic films.

The electroless plating method according to the invention, applied to the fabrication of a thermoelectric device, may comprise the following respective steps:

(1) the step of forming a metallic film made of a metal on which an electroless plating film can be deposited on one of end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

(2) the step of dipping the thermoelectric device block having the

metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on the metallic film and the other end face of the respective thermoelectric semiconductors, on the side thereof, opposite from the end face on which the metallic film is formed;

- 5 (3) the step of removing the metallic film and a portion of the electroless plating film, covering up the metallic film; and
- (4) the step of dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the end face of the respective thermoelectric semiconductors from which the metallic film is removed.
- 10

With the electroless plating methods described above, the following steps (5) to (8) may be substituted for the abovementioned steps (1) to (4):

- (5) the step of causing a metal on which an electroless plating film can be deposited to be in contact with a part of at least one of end faces of respective thermoelectric semiconductors of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;
- 15
- (6) the step of dipping the thermoelectric device block having the metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the respective thermoelectric semiconductors, except the part thereof, in contact with the metal,
- 20
- (7) the step of separating the metal in contact with the respective thermoelectric semiconductors therefrom; and
- 25
- (8) the step of dipping again the thermoelectric device block subjected

to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with the metal.

Further, with the electroless plating methods described above, the following steps (9) and (10) may be substituted for the abovementioned steps (1) to (8):

(9) the step of forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans the respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

(10) the step of dipping the thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on the metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face thereof.

Still further, with the electroless plating methods described above, the following steps (11) and (12) may be substituted for the abovementioned steps (1) to (8):

(11) the step of forming a metallic film made of a metal on which an electroless plating film can be deposited on either an end face or the other end face of respective insulation layers, alternately, on the sides of both end faces of a thermoelectric device block formed integrally with a

plurality of thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans the respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers; and

(12) the step of dipping the thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on the metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face and the other end face thereof.

Yet further, with any of the electroless plating methods comprising the abovementioned steps (1) to (12), use may be made of the thermoelectric device block provided with an exposed outer sidewall face of respective thermoelectric semiconductors positioned at opposite ends in the direction along which the respective thermoelectric semiconductors are arranged, and an electroless plating film may be also formed on the exposed outer sidewall faces as well in the step of forming the electroless plating film.

Further, in the case of applying the electroless plating method according to the invention to the fabrication of a thermoelectric device, the electroless plating method preferably comprises the step of rendering the end face of the thermoelectric device block into a rough surface prior to the step of forming the electroless plating film on the thermoelectric device block.

Still further, the electroless plating method preferably comprises the step of cleaning the thermoelectric device block before or after the step of forming the electroless plating film on the thermoelectric device.

surface of the thermoelectric semiconductor and the metallic film;

Fig. 3 is a sectional view schematically showing a thermoelectric device block to which electroless plating is applied by the invention;

5 Figs. 4 to 8 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a first embodiment of the invention;

10 Figs. 9 to 11 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a second embodiment of the invention;

Figs. 12 and 13 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a third embodiment of the invention;

15 Figs. 14 to 16 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a fourth embodiment of the invention;

Fig. 17 is a sectional view showing a state wherein probes are caused to be in contact with the thermoelectric device block in applying electroless plating to the thermoelectric device block according to the

What is claimed is:

1. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the surface of the object to be plated, without the metallic film formed thereon and the metal in contact therewith.

2. An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied;

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the object to be plated, containing said metallic film or the metal;

removing said metallic film or the metal, and portions of the electroless plating film, covering up the metallic film or the metal, from said object to be plated; and

dipping again the object to be plated subjected to the steps described above in the electroless plating bath.

3. (Amended) An electroless plating method comprising the steps of:

5 forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

10 dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath,

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wherein said object to be plated is made of plural kinds of constituent materials.

4. (Amended) An electroless plating method comprising the steps of:

5 forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

10 dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, wherein said object to be plated is a thermoelectric semiconductor.

5 5. An electroless plating method according to claim 2, wherein said electroless plating film is formed so as to have a dual-layer structure comprised of not less than two metallic films.

6. (Amended) An electroless plating method comprising the steps of:

20 forming a metallic film made of a metal on which an electroless plating film can be deposited on one of end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

25 dipping said thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and the other end face of the respective thermoelectric semiconductors, on the side thereof, opposite from the end face on which the metallic film is formed;

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removing said metallic film and a portion of the electroless plating film covering up the metallic film; and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the end face of the respective thermoelectric semiconductors from which the metallic film is removed.

7. (Amended) An electroless plating method comprising the steps of:

causing a metal on which an electroless plating film can be deposited to be in contact with a part of at least one of end faces of

respective thermoelectric semiconductors of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

5 dipping the thermoelectric device block having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the respective thermoelectric semiconductors, except the part thereof, in contact with said metal,

10 separating the metal in contact with the respective thermoelectric semiconductors therefrom; and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with said metal.

15 8. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans said respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

25 dipping the thermoelectric device block having said metallic film

formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face thereof.

9. (Amended)An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on either an end face or the other end face of respective insulation layers, alternately, on the sides of both end faces of a thermoelectric device block formed integrally with a plurality of thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans the respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers; and

dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face and the other end face thereof.

10. An electroless plating method according to any one of claims 6 to 9, wherein use is made of said thermoelectric device block provided with an exposed outer sidewall face of respective thermoelectric semiconductors positioned at opposite ends in the direction along which the respective thermoelectric semiconductors are arranged, and an electroless plating film is also formed on the exposed outer sidewall faces of respective thermoelectric semiconductors positioned at opposite

ends as well in said step of forming the electroless plating film.

11. An electroless plating method according to any one of claims

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6 to 9, further comprising the step of rendering the end face of the thermoelectric device block into a rough surface prior to the step of forming the electroless plating film on said thermoelectric device block.

12. An electroless plating method according to any one of claims 6 to 9, further comprising the step of cleaning said thermoelectric device block before or after the step of forming the electroless plating film on said thermoelectric device block.

13.(added) An electroless plating method comprising the steps of:
forming a metallic film made of a metal on which an electroless
 10 plating film can be deposited on part of the surface of an object to be
plated, or causing the metal to be in contact with part of the surface of
the object to be plated, made of a constituent material to which an
electroless plating can not be applied;

dipping the object to be plated having the metallic film formed
 15 thereon or having the metal in contact therewith in an electroless plating
bath, and forming an electroless plating film on the entire surface of the
object to be plated, containing the metallic film or the metal;

removing the metallic film or the metal, and portions of the
electroless plating film, covering up the metallic film or the metal, from
 20 the object to be plated; and

dipping again the object to be plated subjected to the steps
described above in the electroless plating bath, wherein the object to be
plated is made of plural kinds of constituent materials.

14. (added) An electroless plating method comprising the steps of:
 25 forming a metallic film made of a metal on which an electroless
plating film can be deposited on part of the surface of an object to be
plated, or causing the metal to be in contact with part of the surface of

16.(added) An electroless plating method according to claim 1,
wherein use is made of a metal or a semiconductor, to which an

electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

5 17.(added) An electroless plating method according to claim 2, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

10 18. (added) An electroless plating method according to claim 3, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

19. (added) An electroless plating method according to claim 13, wherein use is made of a metal or a semiconductor, to which an electroless plating can not be applied, as the constituent material to which an electroless plating can not be applied.

15 20. (added) An electroless plating method according to any one of claims 1 to 4, claims 6 to 9, and claims 13 to 15, wherein use is made of palladium, platinum or nickel as the metal on which the electroless plating film can be deposited.

20 21. (added) An electroless plating method according to claim 15, wherein use is made of an insulating resin for the insulators.

22. (added) An electroless plating method according to any one of claims 6 to 9, wherein use is made of an insulating resin for the insulation layers.

10/pyls

DESCRIPTION

ELECTROLESS PLATING METHOD

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TECHNICAL FIELD

The invention relates to an electroless plating method for applying electroless plating to an object to be plated, made of a constituent material to which an electroless plating can not be directly applied, and in particular, to an electroless plating method suited for forming a conductive film on end faces of respective thermoelectric semiconductors of a thermoelectric device block.

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BACKGROUND TECHNOLOGY

As a thermoelectric device generates a voltage if the opposite ends thereof are maintained at different temperatures, the same is utilized for thermoelectric power generation, and conversely, if electric current is caused to flow therethrough, an exothermic reaction occurs at one end thereof while an endothermic reaction occurs at the other end thereof. Accordingly, the same is also utilized in a cooling apparatus, and so forth, making use of an endothermic phenomenon. Because such a thermoelectric device as described above is simple in construction, and has an advantage over other electric power generators in implementation of miniaturization, and so forth, hopes run high that the same will be applied to portable electronic equipment such as an electronic wrist watch.

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The thermoelectric device is made up of a plurality of thermocouples arranged in series, each composed of a p-type

A thermoelectric device 10 shown in Fig. 19 has a thermoelectric device block 11 wherein p-type thermoelectric semiconductors 1 and n-type thermoelectric semiconductors 1 are alternately disposed with an insulation layer 4 made of epoxy resin, interposed therebetween, respectively. A conductive film 3 provided on an end face of the respective thermoelectric semiconductors 1, on opposite sides thereof, is connected with a wiring electrode 6 made of copper or gold, provided on substrates 7, respectively, through the intermediary of respective connection layers 5, thereby rendering the thermoelectric device block 11 electrically continuous with the substrates 7, and connecting the respective thermoelectric semiconductors 1 with each other in series.

Prior to connecting the thermoelectric device 10 with the substrates 7, the conductive film 3 is formed on the end face of the respective thermoelectric semiconductors 1, on the opposite sides thereof, to be connected with the respective wiring electrodes 6. This is necessary for the following reasons.

The connection layers 5 are provided in order to ensure electrical continuity between the respective thermoelectric semiconductors 1 and the respective wiring electrodes 6, however, if the connection layers 5 are formed of solder, tin contained therein is diffused into the respective thermoelectric semiconductors 1, causing deterioration in performance of the thermoelectric device 10. Accordingly, it is necessary to form the conductive films 3 for elimination of such a risk and to ensure wettability of solder. Further, in the case of forming the connection

layers 5 from a conductive adhesive, it is necessary to form the conductive films 3 having a low contact resistance against the conductive adhesive because of a large contact resistance between the respective thermoelectric semiconductors 1 and the conductive adhesive.

In the case of forming a metallic film on a thermoelectric semiconductor, serving as a conductive film, plating is generally adopted. In applying plating, an electroless plating method using a self-catalyzing type electroless plating bath is advantageous in terms of productivity. It is not possible, however, to apply electroless plating to a thermoelectric semiconductor composed of an intermetallic compound of a bismuth-tellurium base or an antimony-tellurium base.

For this reason, in the case of forming a conductive film on the surface of material such as a thermoelectric semiconductor to which it is not possible to apply electroless plating, it has been a normal practice to apply electroplating thereto.

For the formation of the conductive film on the surface of the thermoelectric semiconductor by electroplating, however, electric power needs to be supplied to the thermoelectric semiconductor, which has caused a problem in that the thickness of a plating film formed becomes thinner according as a distance from the point of power supply increases due to a voltage drop caused by a resistance value of the thermoelectric semiconductor. This has resulted in fluctuation in the thickness of the conductive film made up of the plating film, thereby impairing an effect of preventing diffusion of tin contained in solder, and adversely affecting wettability of solder.

In JP11-186619, a method of applying electroless plating by

In particular, the thermoelectric device comprises thermoelectric
25 semiconductors which are very small in size, and has sometimes a
minuscule structure wherein the thermoelectric semiconductors are
disposed at an interval between the adjacent thermoelectric

semiconductors, in a range of several to several tens of μm . The more minuscule the structure of the thermoelectric device, the more difficult it becomes to form the conductive films selectively only on the thermoelectric semiconductors. It is therefore a major problem in the
5 fabrication of the thermoelectric device to selectively form the conductive films by electroless plating.

The invention has been developed to solve those problems, and an object of the invention is to provide an electroless plating method whereby conductive films can be formed even on the surface of a
10 constituent material to which it is not possible to apply electroless plating, and further, to selectively form the conductive films uniform in thickness on end faces of respective thermoelectric semiconductors formed of a constituent material to the surface of which it is not possible to apply electroless plating, thereby enhancing productivity and
15 reliability of a thermoelectric device as fabricated.

DISCLOSURE OF THE INVENTION

An electroless plating method according to the invention comprises the steps of forming a metallic film made of a metal on which
20 an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied, and dipping the object to be plated having the metallic film formed thereon or having the metal in
25 contact therewith in an electroless plating bath.

Further, the electroless plating method according to the invention may comprise the steps of forming a metallic film made of a metal on

which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied, dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the object to be plated, containing the metallic film or the metal, removing the metallic film or the metal, and portions of the electroless plating film, covering up the metallic film or the metal, from the object to be plated, and dipping again the object to be plated subjected to the steps described above in the electroless plating bath.

With any of the electroless plating methods described above, the object to be plated may be made of plural kinds of constituent materials or may be a thermoelectric semiconductor.

Further, with any of the electroless plating methods described above, the electroless plating film may be formed so as to have a dual-layer structure comprised of not less than two metallic films.

The electroless plating method according to the invention, applied to the fabrication of a thermoelectric device, may comprise the following respective steps:

(1) the step of forming a metallic film made of a metal on which an electroless plating film can be deposited on one of end faces of a thermoelectric device block formed integrally with a plurality of bar-shaped thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

(2) the step of dipping the thermoelectric device block having the

5 (3) the step of removing the metallic film and a portion of the electroless plating film, covering up the metallic film; and

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With the electroless plating methods described above, the following steps (5) to (8) may be substituted for the abovementioned steps (1) to (4):

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(8) the step of dipping again the thermoelectric device block subjected

to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with the metal.

Further, with the electroless plating methods described above, the following steps (9) and (10) may be substituted for the abovementioned steps (1) to (8):

(9) the step of forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of bar-shaped thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans the respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

(10) the step of dipping the thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on the metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face thereof.

Still further, with the electroless plating methods described above, the following steps (11) and (12) may be substituted for the abovementioned steps (1) to (8):

(11) the step of forming a metallic film made of a metal on which an electroless plating film can be deposited on either an end face or the other end face of respective insulation layers, alternately, on the sides of both end faces of a thermoelectric device block formed integrally with a

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block.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a sectional view showing a state wherein a metallic film
made of a metal on which an electroless plating film can be deposited is
formed on part of the surface of a thermoelectric semiconductor by the
invention;

Fig. 2 is a sectional view showing a state wherein a conductive film according to an electroless plating film is formed on the entire surface of the thermoelectric semiconductor and the metallic film;

Fig. 3 is a sectional view schematically showing a thermoelectric device block to which electroless plating is applied by the invention;

15 Figs. 4 to 8 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a first embodiment of the invention;

Figs. 9 to 11 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a second embodiment of the invention;

Figs. 12 and 13 are sectional views sequentially showing
20 respective steps of applying electroless plating to the thermoelectric
device block according to a third embodiment of the invention;

Figs. 14 to 16 are sectional views sequentially showing respective steps of applying electroless plating to the thermoelectric device block according to a fourth embodiment of the invention;

Fig. 17 is a sectional view showing a state wherein probes are caused to be in contact with the thermoelectric device block in applying electroless plating to the thermoelectric device block according to the

first embodiment of the invention;

Fig. 18 is a sectional view showing state wherein the metallic film is formed on the another thermoelectric device block in applying electroless plating to the thermoelectric device block according to the fourth embodiment of the invention; and

Fig. 19 is a sectional view schematically showing the construction of a common type thermoelectric device.

BEST MODE FOR CARRYING OUT THE INVENTION

10 Preferred embodiments of an electroless plating method according to the invention are described hereinafter with reference to the accompanying drawings. First, the basic embodiment of the electroless plating method according to the invention is described with reference to Figs. 1 and 2.

15 **Basic Embodiment: Figs. 1 and 2**

Fig. 1 is a sectional view showing a state wherein a metallic film made of a metal on which an electroless plating film can be deposited is formed on part of the surface of a thermoelectric semiconductor which is an example of an object to be plated, made of a constituent material to which an electroless plating can not be directly applied.

A thermoelectric semiconductor 8 is formed in a block shape, and is generally made of an intermetallic compound selected from the group consisting of bismuth-tellurium based compound, antimony-tellurium based compound, bismuth-tellurium-antimony based compound, bismuth-tellurium-selenium based compound, and so forth, but the same may be formed of an intermetallic compound selected from the group consisting of lead-germanium based compound, silicon-germanium

based compound, and so forth, although not limited particularly to those mentioned above.

Thereafter, the thermoelectric semiconductor 8 with the metallic film 2 formed thereon is dipped in an electroless plating bath (not shown), whereupon an electroless plating film is first deposited on the surface of the metallic film 2. Because the metallic film 2 is in contact with the thermoelectric semiconductor 8 at this point in time, the potential of the thermoelectric semiconductor 8 relative to the electroless plating bath (a condition for effecting transfer of electrons with the metal in electroless plating bath) undergoes a change, thereby allowing the electroless plating film to be deposited on the thermoelectric semiconductor 8. Accordingly, the electroless plating film deposited from the metallic film 2 spreads out to the thermoelectric

5 In the case of a constituent material to which the electroless
plating can not be directly applied being the aforementioned
thermoelectric semiconductor, the conductive film 3 is preferably
formed of nickel (Ni) highly effective in preventing diffusion of tin,
copper, and so forth into the thermoelectric semiconductor although the
0 constituent material thereof is not limited particularly to nickel.

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An object to be plated which this method is applicable to is not limited to the thermoelectric semiconductor. It becomes possible to

form a conductive film made of a metal having a high conductivity by the electroless plating method even on a metal, cadmium, tungsten, zinc, tin, lead, bismuth, antimony and so forth, to which it has been regarded impossible to apply electroless plating.

Further, instead of forming the metallic film made of the metal on which the electroless plating film can be deposited on part of the surface of the object to be plated as described above, the metal on which the electroless plating film can be deposited may be brought into contact with an object to be plated, such as a thermoelectric semiconductor, and so forth, and with such a contact condition maintained by use of a tool such as a clip, the object to be plated may be dipped in an electroless plating bath. With such a method as well, it is possible to obtain the same effect of forming a conductive film uniform in thickness on the entire surface of the object to be plated. In this case, a clip made of a metal on which an electroless plating film can be deposited may be brought into direct contact with the object to be plated. Further, not the whole, but only part of a clip, coming into contact with the object to be plate, may be formed of a metal on which an electroless plating film can be deposited.

Furthermore, after removing the metallic film 2, and a portion 3a of the conductive film 3, covering the metallic film 2, shown in Fig. 2, the thermoelectric semiconductor 8 may be dipped again in the electroless plating bath. By so doing, the conductive film 3 can be formed on the entire surface of the thermoelectric semiconductor 8.

Embodiments of the electroless plating method according to the invention for applying electroless plating to a thermoelectric device block will be described in detail hereinafter with reference to Figs. 3 to

18. In these figures, parts corresponding to those in Fig. 19 are denoted by like reference numerals.

First Embodiment: Figs. 3 to 8, and Fig. 17

First, a first embodiment of the invention is described with reference to Figs. 3 to 8, and Fig. 17. This method for applying electroless plating to a thermoelectric device block represents an application of the electroless plating method according to the invention as described hereinbefore.

Fig.3 is a sectional view of a thermoelectric device block 11 which is an object to be plated. With the thermoelectric device block 11, p-type and n-type thermoelectric semiconductors 1, each in a bar-like shape, are alternately disposed at an interval in a range of about 5 to 80 μm with an insulation layer 4 made of epoxy resin, interposed therebetween, respectively, and the respective thermoelectric semiconductors 1 adjacent to each other are isolated by the insulation layer 4.

As with the thermoelectric semiconductors 8 described in the foregoing, the thermoelectric semiconductors 1 are made of an intermetallic compound in common use, selected from the group consisting of bismuth-tellurium based compound, antimony-tellurium based compound, bismuth-tellurium-antimony based compound, bismuth-tellurium-selenium based compound, or an intermetallic compound selected from the group consisting of lead-germanium based compound, silicon-germanium based compound, and so forth, although not limited to those mentioned above.

The thermoelectric device block 11 is formed as follows. First, a thermoelectric semiconductor block (not shown) worked into a

Subsequently, the thermoelectric device block 11 with the metallic

film 2 formed thereon is dipped in an electroless plating bath, whereupon deposition reaction of an electroless plating film occurs to the surface of the metallic film 2, as shown in Fig. 5, and simultaneously, the potential of the respective thermoelectric semiconductor 1 relative to the electroless plating bath (a condition for effecting transfer of electrons with the metal in electroless plating bath) undergoes a change, so that deposition reaction of the electroless plating film occurs to the end face 1b as well, on the side of the respective thermoelectric semiconductor 1, where the metallic film 2 is not formed. Thus, a conductive film 3 which is the electroless plating film can be formed directly only on the end face 1b of the respective thermoelectric semiconductors 1.

Then, the metallic film 2 and a portion of the conductive film 3, formed on top of the metallic film 2 so as to cover up the same, is removed by etching, as shown in Fig. 6, and thereafter, the thermoelectric device block 11 is dipped again in the electroless plating bath, whereupon a conductive film 3 can be formed selectively only on the end face 1a of the respective thermoelectric semiconductors 1, exposed by removing the metallic film 2 by means of etching, as shown in Fig. 7. With such a method as described above, since the conductive film 3 will not be formed on unnecessary parts such as the insulation layers 4, electrical insulation between the respective thermoelectric semiconductors 1 can be ensured, so that a highly reliable thermoelectric device provided with the conductive film 3 formed only on both the end faces 1a, 1b of the respective thermoelectric semiconductors 1 can be obtained.

Further, instead of forming the conductive films 3 on the

thermoelectric device block 11 as described in the foregoing, the following process may be adopted. First, a probe 14 made of a metal on which an electroless plating film can be deposited, in the shape of a needle as shown in Fig. 17, is caused to be in contact with a part of the end face 1b of the respective thermoelectric semiconductors 1, or a plate (not shown) made of a metal on which an electroless plating film can be deposited, formed in a shape corresponding to the end face 11a (11b) of the thermoelectric device block 11, is caused to be in contact with the end face 1b of the respective thermoelectric semiconductors 1. Thereafter, the thermoelectric device block 11 with the probes 14 in contact therewith is dipped in an electroless plating bath, thereby causing an electroless plating film to be deposited on the entire surface of the respective thermoelectric semiconductors 1, except for a part thereof, in contact with the probe 14. Subsequently, after separating the probes 14 from the respective thermoelectric semiconductors 1, the thermoelectric device block 11 is dipped again in the electroless plating bath, thereby causing an electroless plating film to be deposited on the part of the surface of the respective thermoelectric semiconductors 1, in contact with the probe 14. In this way, it is also possible to form the conductive film 3 only on both the end faces 1a, 1b of the respective thermoelectric semiconductors 1.

At the time when the previously described etching is performed, a photoresist (not shown) is applied to the entire surface of the thermoelectric device block 11, on the side of the end face 11b thereof, shown in Fig. 5. The reason for this is because the conductive film 3 already formed selectively on the end face 1b, on one side of the respective thermoelectric semiconductors 1, needs to be protected by the

Subsequently, as shown in Fig. 8, connection layers 9 made of a connecting material such as a conductive adhesive or a solder paste are formed by the printing method on the thermoelectric device block 11 provided with the conductive film 3 formed on the end faces 1a, 1b, respectively, on opposite sides of the respective thermoelectric semiconductors 1, shown in Fig. 7. The p-type thermoelectric semiconductors 1 and the n-type thermoelectric semiconductors 1 are alternately connected with each other, respectively, via the respective connection layers 9, and upon applying heat treatment thereto, the

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Thereafter, as shown by the phantom lines in Fig. 10, a connection layer made of a connecting material such as a conductive adhesive or a

solder paste is formed by the printing method on the end face 1b of the respective thermoelectric semiconductors 1, with the conductive film 3 selectively formed thereon, thereby alternately connecting the respective p-type thermoelectric semiconductors 1 with the respective n-type thermoelectric semiconductors 1. Upon applying heat treatment thereto, there is obtained a thermoelectric device wherein the respective thermoelectric semiconductors 1 are electrically connected together in series.

For obtaining the thermoelectric device by connecting the respective thermoelectric semiconductors 1 in series, a substrate 7 with a wiring electrode 6 made of copper or gold, formed thereon, may be used, and by electrically connecting the respective conductive films 3 on the end face 11a side of the thermoelectric device block 11 with the wiring electrode 6 on the substrate 7 through the intermediary of respective connection layers 5 formed of solder, a conductive adhesive, an anisotropic conductive adhesive, or so forth, as shown in Fig. 11, the respective thermoelectric semiconductors 1 may be connected with each other in series, thereby completing a thermoelectric device 21.

In contrast with the first embodiment as previously described, according to the second embodiment, a processing step of removing the metallic film 2 formed on the end face 11a, on one side of the thermoelectric device block 11, is not required, thereby enabling a process up to the completion of the thermoelectric device to be shortened. Accordingly, productivity in fabrication of the thermoelectric device can be improved.

Third Embodiment: Fig.3 and Figs.12 and 13

Subsequently, a third embodiment of a method for applying

electroless plating according to the invention to a thermoelectric device block is described hereinafter with reference to Fig.3 and Figs.12 and 13.

With this embodiment, use is made of the thermoelectric device block 11 shown in Fig. 3 as with the case of the first embodiment, and for other parts such as metallic films, conductive films, an electroless plating bath, and so forth, use is also made of the same constituent materials as those used for the corresponding parts in the first embodiment.

First, metallic films 2 on which an electroless plating film can be deposited are formed on end faces 11a, 11b of the thermoelectric device block 11 shown in Fig. 3, on opposite sides thereof, by the vacuum deposition method, the sputtering method or so forth, as shown in Fig. 12. With the use of a metal mask, and so forth, each of the metallic films 2 is formed selectively only on end face 4a, and end face 4b of respective insulation layers 4, in an alternate and staggered sequence, that is, on those where the metallic film 2 is required for connecting respective p-type thermoelectric semiconductors 1 and respective n-type thermoelectric semiconductors 1, disposed on opposite sides of the respective insulation layers 4, with each other, thereby connecting the respective thermoelectric semiconductors 1 in series. More specifically, each of the metallic films 2 is formed so as to span a part of the end faces 1a or the end faces 1b of the adjacent thermoelectric semiconductors 1 with the respective insulation layers 4 interposed therebetween, and also, on the end face 4a and the other end face 4b of the respective insulation layers 4, alternately.

Subsequently, the thermoelectric device block 11 provided with

the outer sidewall face of thermoelectric semiconductors 1 among respective thermoelectric semiconductors 1, positioned at opposite ends in the direction of arrangement thereof, is not coated with an insulation layer 4 so as to be exposed as shown Fig. 14, however, for other parts such as metallic films, conductive films, an electroless plating bath, and so forth, use is made of the same constituent materials as those used for the corresponding parts in the first embodiment.

With this embodiment, a metallic film 2 is first formed on an end face 1a or 1b of the respective thermoelectric semiconductors 1 in the same way as in any of the first to third embodiments. In the case of forming the metallic films 2 in the same way as in the third embodiment, each of the metallic films 2 on which an electroless plating film can be deposited is formed on an end face 4a and the other end face 4b of the respective insulation layers 4 of the thermoelectric device block 15 alternately as to span a part of the end faces 1a or the end faces 1b of the adjacent thermoelectric semiconductors 1 with the respective insulation layers 4 interposed therebetween, as shown in Fig. 14. In the case of forming the metallic film 2 in the same way as in the first embodiment, the metallic film 2 are formed as shown in Fig. 4. In the case of forming the metallic films 2 in the same way as in the second embodiment, the metallic films 2 are formed as shown in Fig. 18.

Subsequently, this thermoelectric device block 15 provided with the metallic films 2 is dipped in an electroless plating bath, whereupon deposition reaction of an electroless plating film occurs to the surface of the respective metallic films 2, and simultaneously, deposition reaction of an electroless plating film occurs to the end face 1a and 1b of the thermoelectric semiconductors 1 with the metallic film 2 formed on (in

contact with) part thereof, and also to the outer sidewall face as exposed of the respective thermoelectric semiconductors 1 positioned on the outermost sides the thermoelectric device block 15 (at opposite ends in the direction along which the respective thermoelectric semiconductors 1 are arranged). Thus, a conductive film 3 can be formed on the
 5 respective metallic films 2, the end face 1a and 1b of the respective thermoelectric semiconductors 1, on opposite sides thereof, and the outer sidewall face as exposed of the respective thermoelectric semiconductors 1 positioned at the opposite ends except for an end face of respective insulation layers 4 without the metallic film 2 formed
 10 thereon, thereby enabling the respective thermoelectric semiconductors 1 to be connected in series.

Thereafter, after forming connection layers 19 made of a connecting material such as a conductive adhesive, solder or so forth, the thermoelectric device block 15 with the conductive films 3 formed
 15 thereon is mounted on a substrate 7 with a wiring electrode 6 formed thereon as shown in Fig. 16. The respective conductive films 3 of the thermoelectric device block 15 are thereby electrically connected with the wiring electrode 6, thus obtaining a thermoelectric device 23. In
 20 this case, with the thermoelectric device block 15 (Fig. 15), since the conductive film 3 is also formed on the outer sidewall face as exposed of the respective thermoelectric semiconductors 1 positioned at the opposite ends in the direction of arrangement thereof, a contact area of the connection layers 19 can be enlarged. As a result, connection of
 25 the wiring electrode 6 with the respective conductive films 3 can be implemented with ease, further enabling a connection condition to be ensured.

semiconductors by applying the invention to a method of fabricating a thermoelectric device. Accordingly, the conductive films having an object of providing the thermoelectric device with the connection layer for the respective thermoelectric semiconductors, and having an effect of preventing diffusion of tin, copper and so forth into the respective thermoelectric semiconductors can be easily formed to a uniform thickness on both the end faces of the respective thermoelectric semiconductors, so that productivity and reliability of the thermoelectric device can be improved.

What is claimed is:

1. An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath.

2. An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied;

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the object to be plated, containing said metallic film or the metal;

removing said metallic film or the metal, and portions of the electroless plating film, covering up the metallic film or the metal, from said object to be plated; and

dipping again the object to be plated subjected to the steps described above in the electroless plating bath.

3. An electroless plating method according to claims 1 or 2,

respective thermoelectric semiconductors of a thermoelectric device block formed integrally with a plurality of bar-shaped thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

5 dipping the thermoelectric device block having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the respective thermoelectric semiconductors, except the part thereof, in contact with said metal,

10 separating the metal in contact with the respective thermoelectric semiconductors therefrom; and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with said metal.

8. An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of bar-shaped thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans said respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless

6 to 9, further comprising the step of rendering the end face of the thermoelectric device block into a rough surface prior to the step of forming the electroless plating film on said thermoelectric device block.

12. An electroless plating method according to any one of claims 5 6 to 9, further comprising the step of cleaning said thermoelectric device block before or after the step of forming the electroless plating film on said thermoelectric device block.

A metallic film (2) made of a metal on which an electroless plating film can be deposited is formed on part of the surface of a thermoelectric semiconductor (8) which is an object to be plated, made of a constituent material to which an electroless plating can not be directly applied, and subsequently, the thermoelectric semiconductor (8) is dipped in an electroless plating bath, whereupon a conductive film (3) having a uniform thickness, made up of an electroless plating film, is formed on the entire surface of the thermoelectric semiconductor (8) containing the surface of the metallic film (2).

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FIG. 1

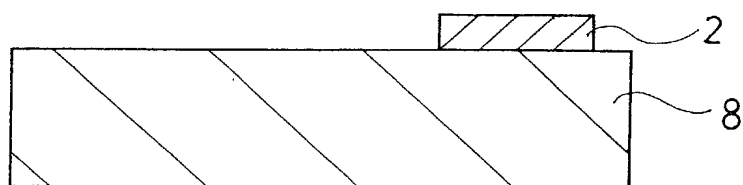
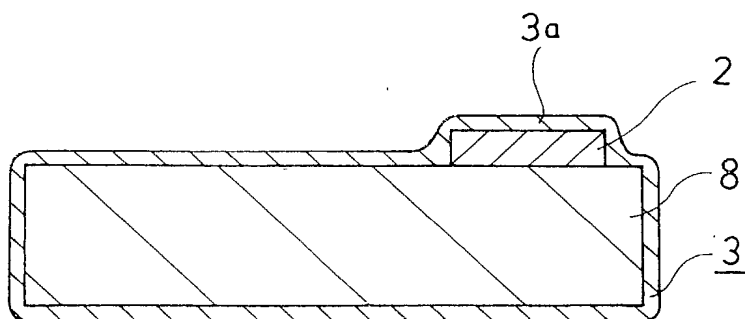


FIG. 2



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FIG. 3

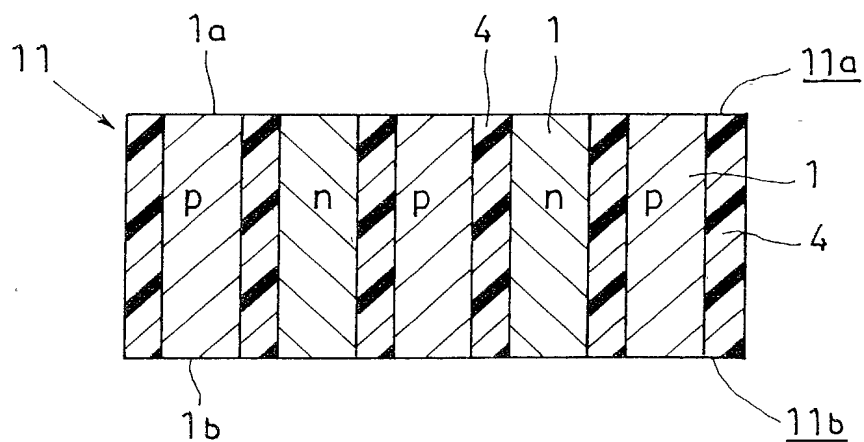
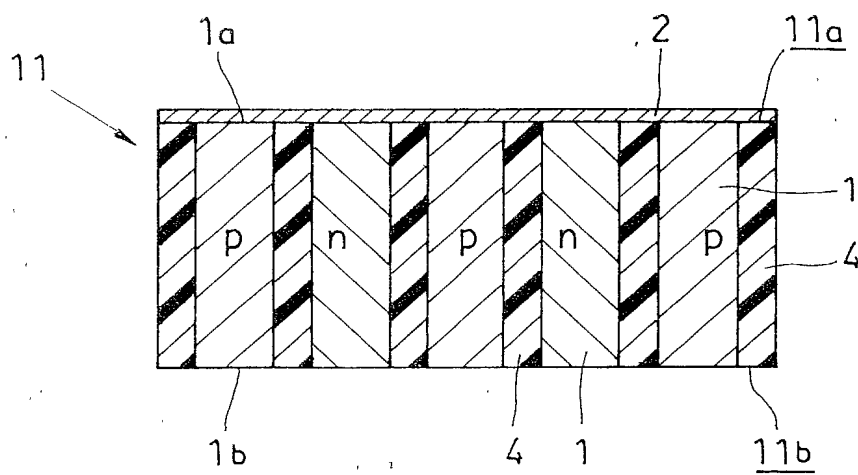


FIG. 4



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FIG. 5

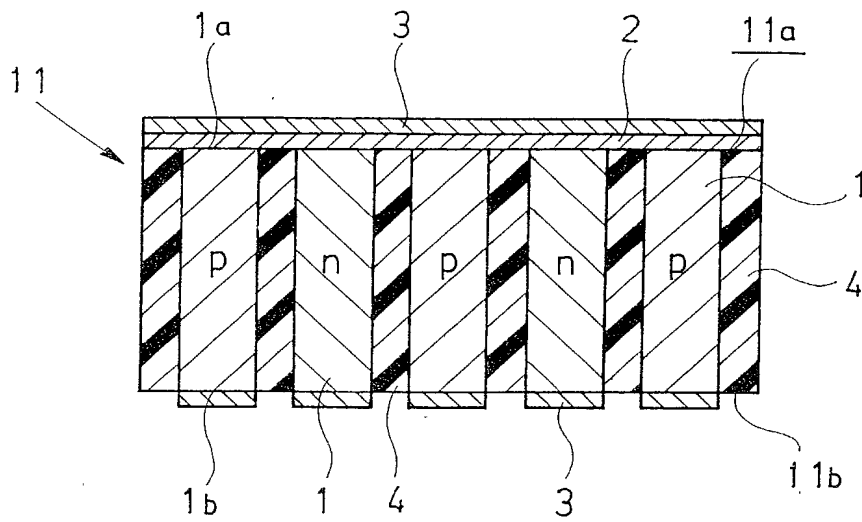
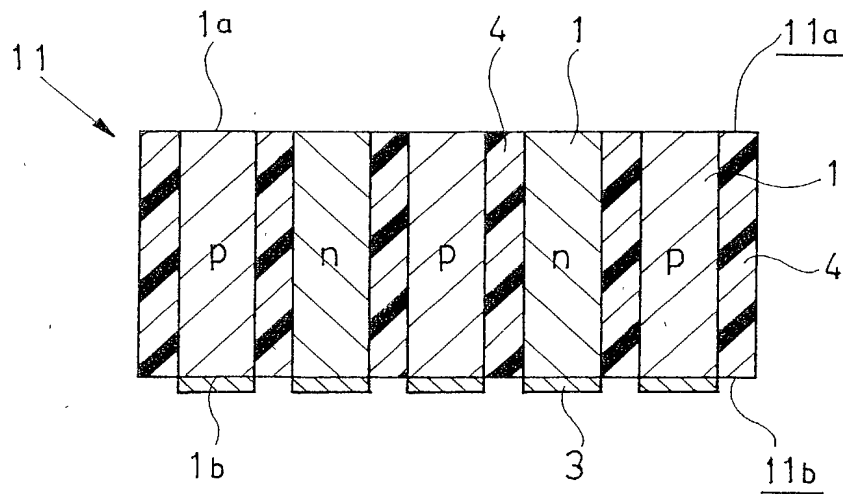


FIG. 6



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FIG. 7

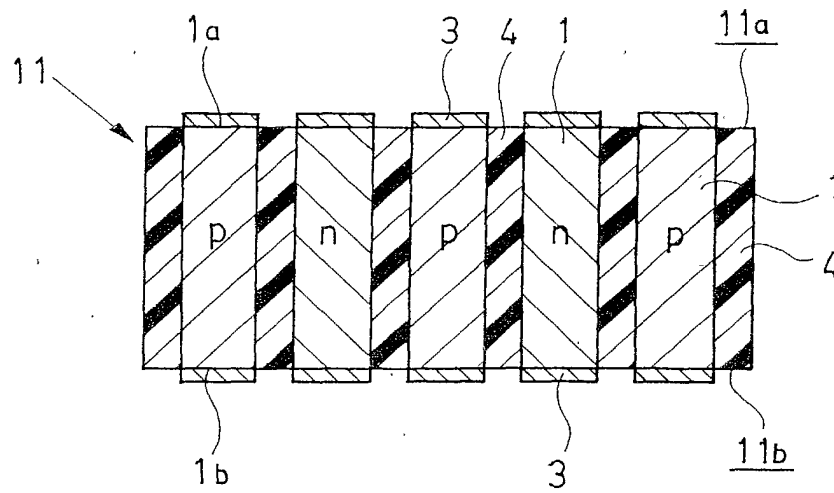
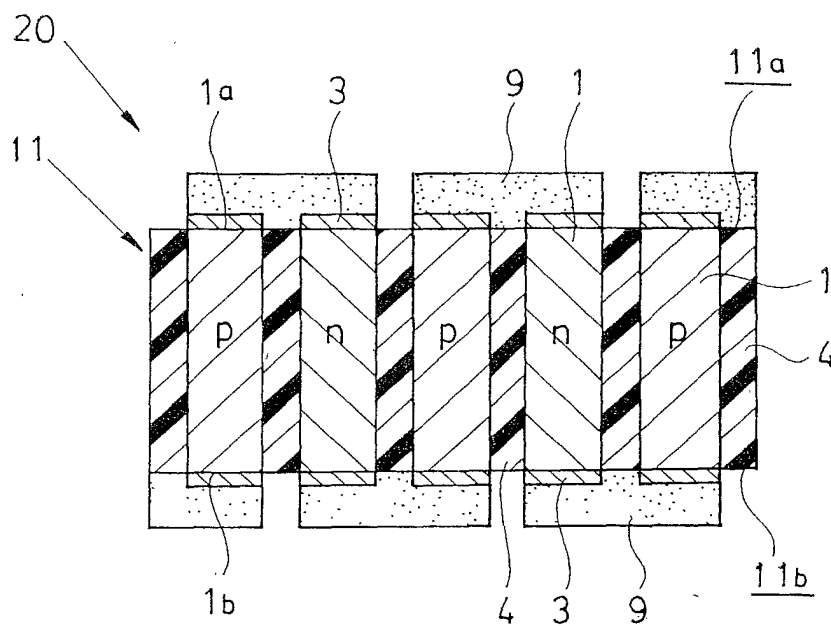


FIG. 8



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FIG. 9

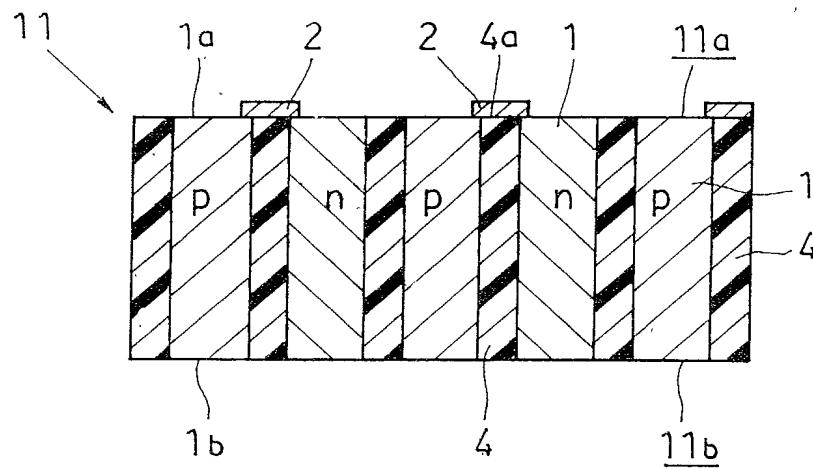
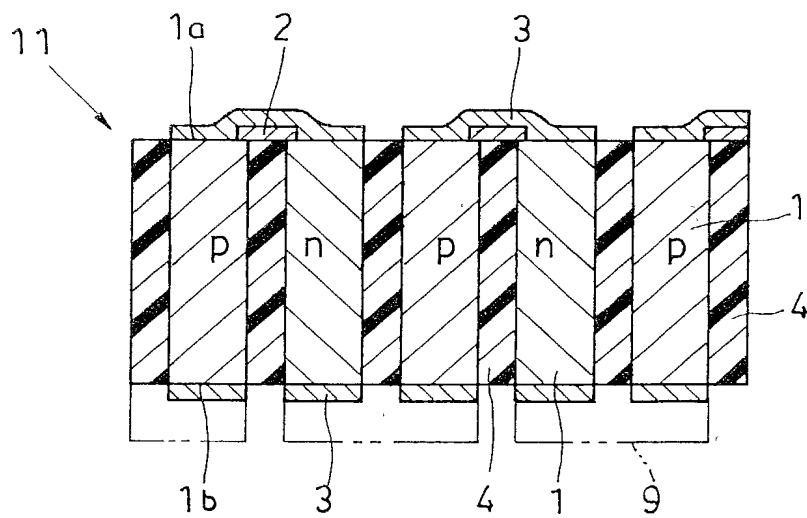


FIG. 10



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FIG. 11

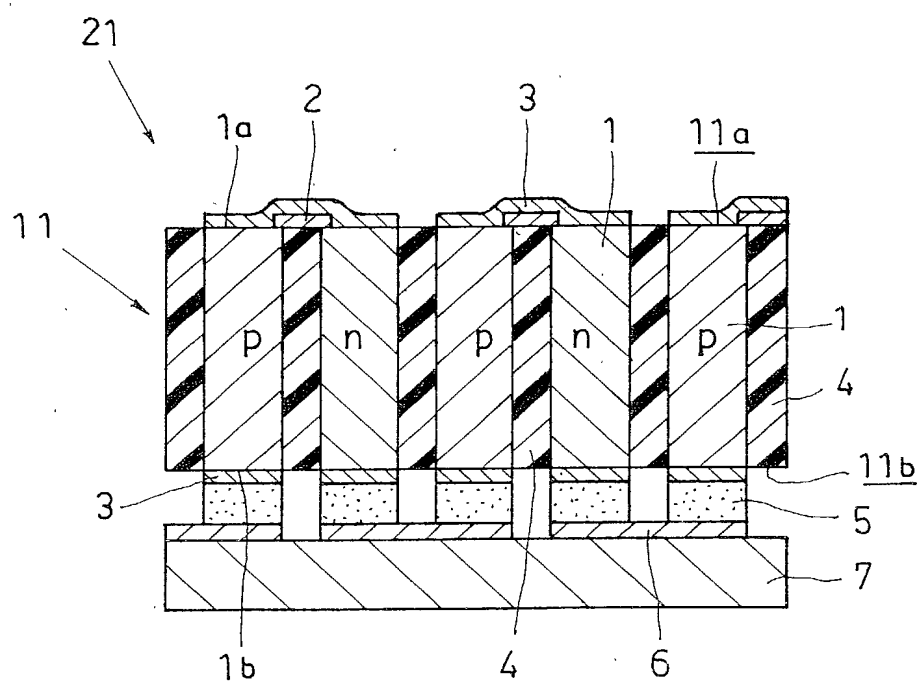
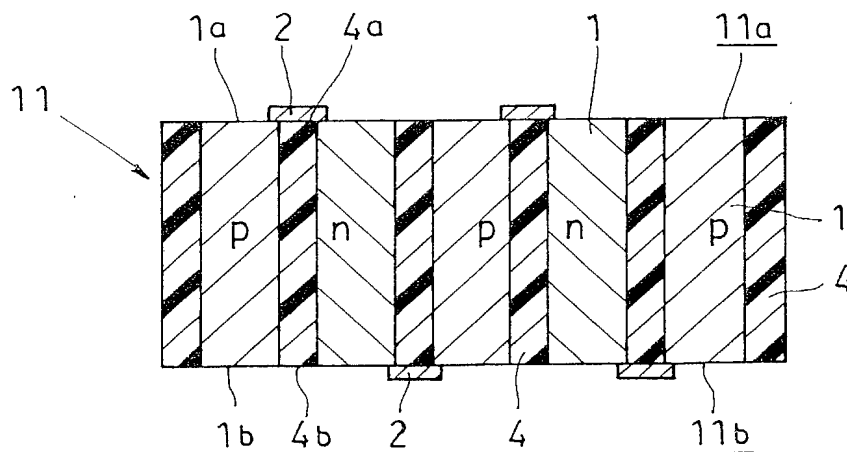


FIG. 12



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FIG. 13

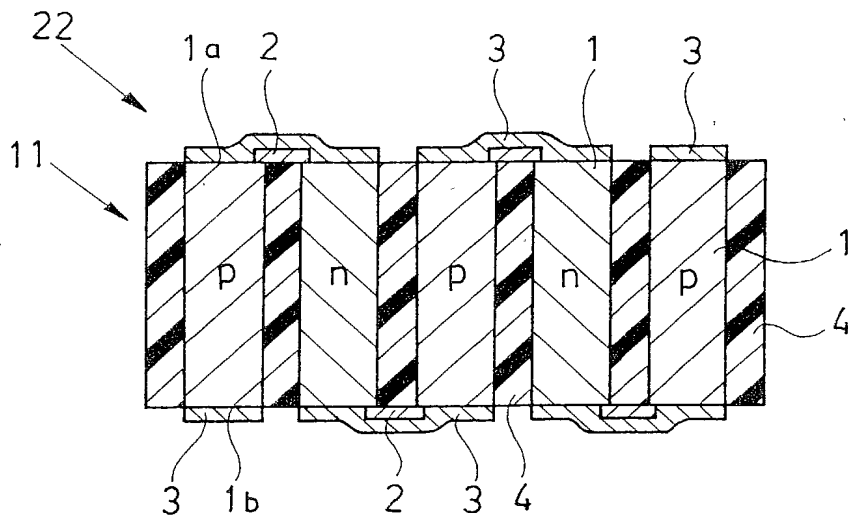
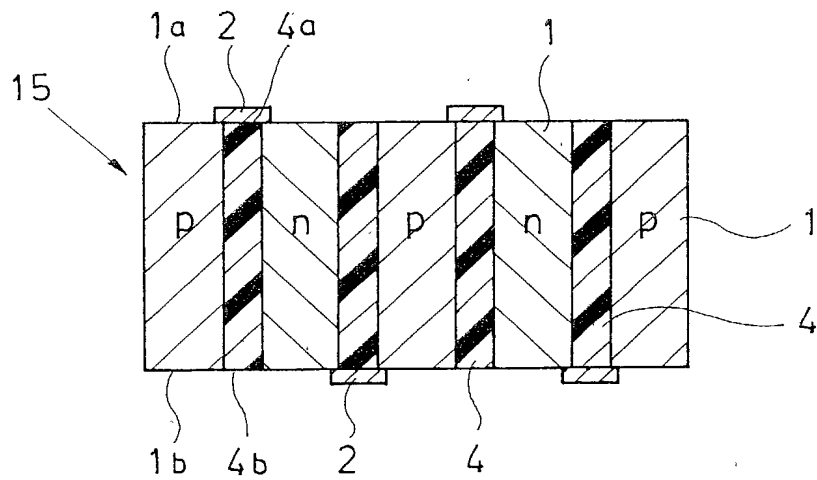


FIG. 14



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FIG. 15

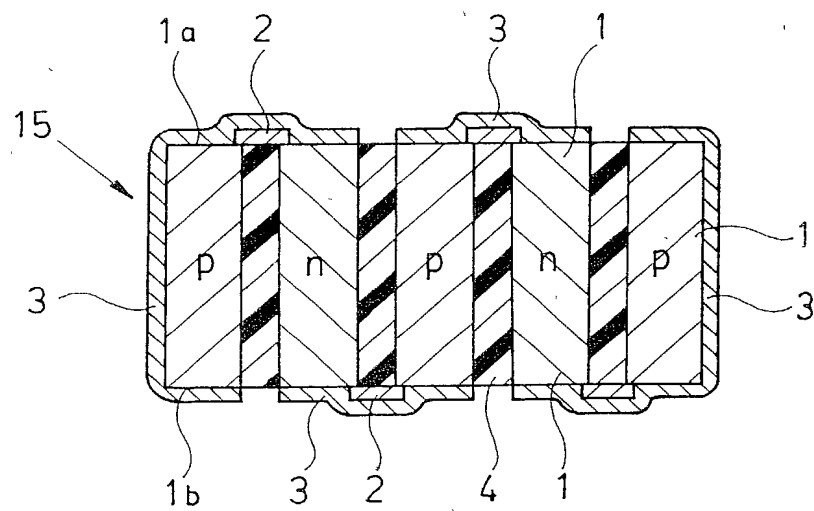
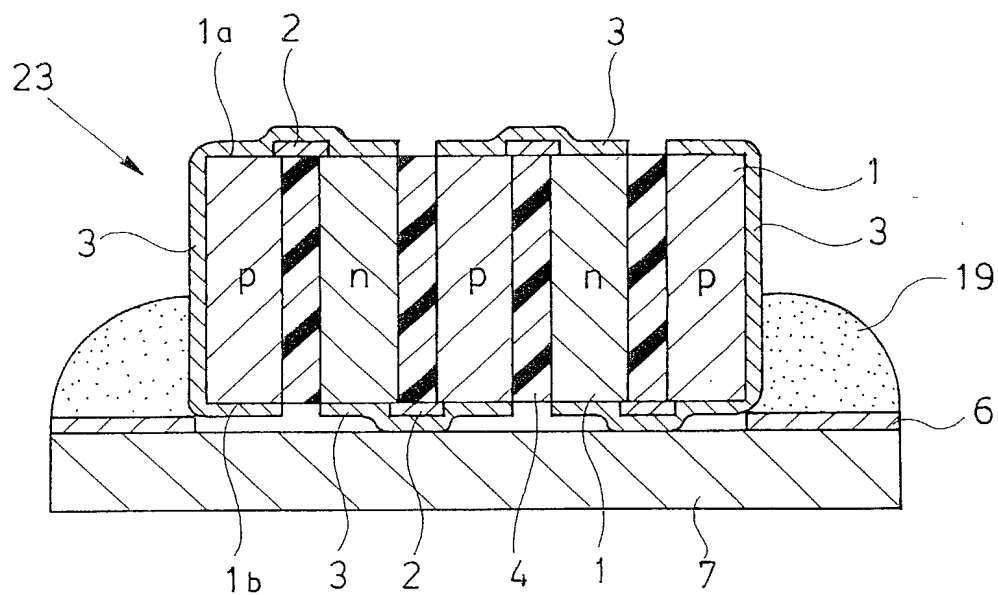


FIG. 16



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FIG. 17

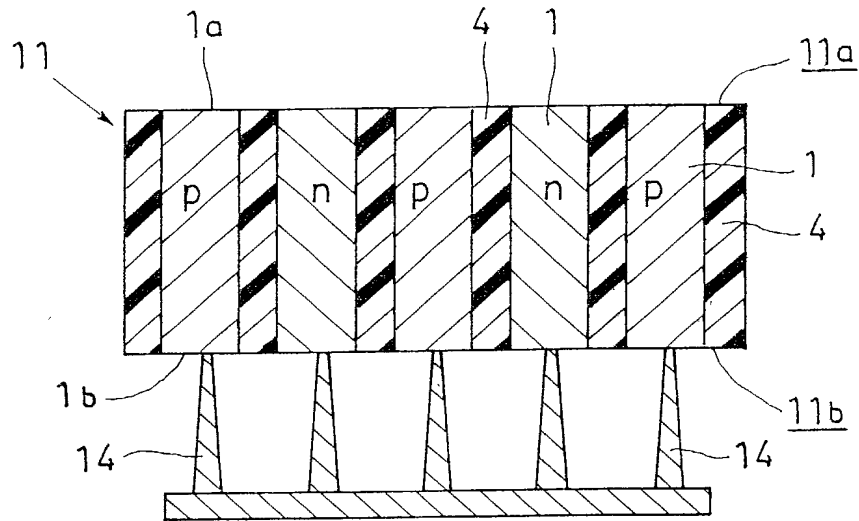
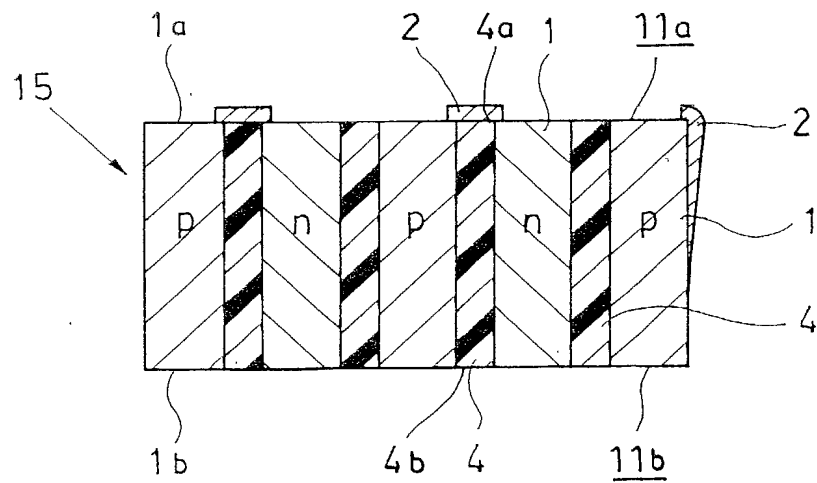
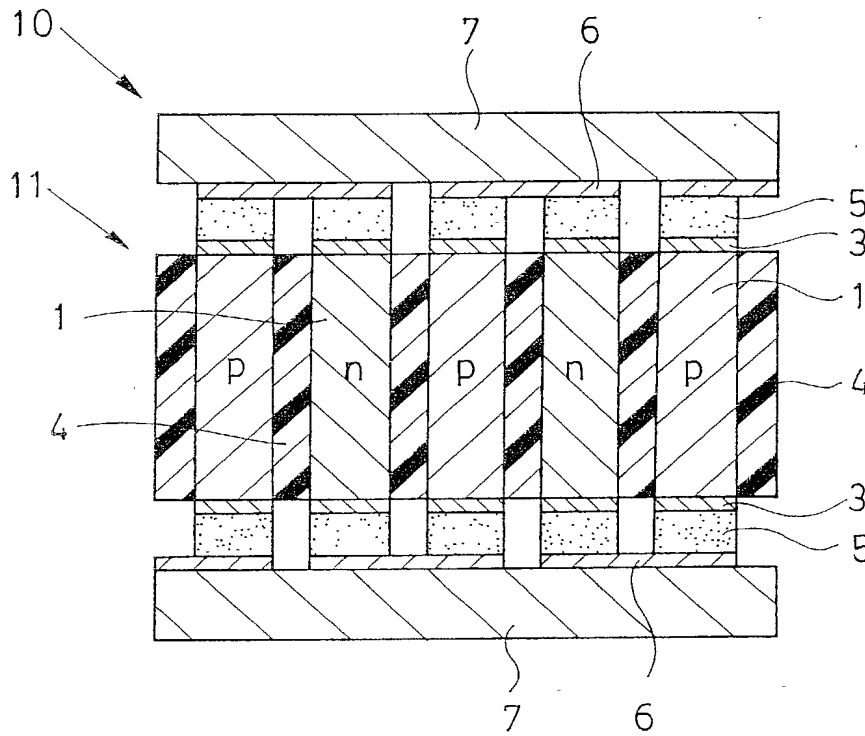


FIG. 18



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FIG. 19
PRIOR ART



Declaration For U.S. Patent Application

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention **entitled**
(Insert Title) ELECTROLESS PLATING METHOD

the specification of which is attached hereto unless the following is checked:



was filed on September 22, 2000 as United States Application Number or PCT International
Application Number PCT/JP00/06504 and was amended on July 11, 2001
(if applicable).

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claim(s), as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, § 119 (a) - (d) of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

(List prior foreign applications. See note A on back of this page)	Patent Appln. <u>11-272610</u> (Number)	<u>JAPAN</u> (Country)	<u>27/September/1999</u> (Day/Month/Year Filed)	Priority Claimed <input checked="" type="checkbox"/> Yes <input type="checkbox"/> No
	Patent Appln. <u>2000-52762</u> (Number)	<u>JAPAN</u> (Country)	<u>29/February/2000</u> (Day/Month/Year Filed)	<input checked="" type="checkbox"/> Yes <input type="checkbox"/> No
	_____ (Number)	_____ (Country)	_____ (Day/Month/Year Filed)	<input type="checkbox"/> Yes <input type="checkbox"/> No
	_____ (Number)	_____ (Country)	_____ (Day/Month/Year Filed)	<input type="checkbox"/> Yes <input type="checkbox"/> No

(See note B on back of this page)

☐ See attached list for additional prior foreign applications

I hereby claim the benefit under Title 35, United States Code, § 119(e) of any United States provisional application(s) listed below.

_____ (Application Number)	_____ (Filing Date)
_____ (Application Number)	_____ (Filing Date)

I hereby claim the benefit under Title 35, United States Code, § 120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of the application:

(List Prior U.S. Applications)	(Application Serial Number)	(Filing Date)	(Status) (patented, pending, abandoned)
	_____ (Application Serial Number)	_____ (Filing Date)	_____ (Status) (patented, pending, abandoned)

I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

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Washington, D.C. 20006
Telephone: (202) 659-2930 Fax: (202) 887-0357

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Title 18 of the United States Code, § 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

1-00
(See note
C above)

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Full name of second inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____

Full name of third inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____

Full name of fourth inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____

Full name of fifth inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____

Full name of sixth inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____

Full name of seventh inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____

Full name of eighth inventor (given name, family name) _____

Inventor's Signature _____ Date _____

Residence _____ Citizenship _____

Post Office Address _____